10 DIODE

1. GENERAL PURPOSE & SWITCHING

SPEC / DEVICE	V_{RM} (V)	I_{FM} (mA)	I_O (mA)	P (mW)	T_j (°C)	V_F MAX (V)	V_F I_F (mA)	I_R MAX (uA)	I_R V_R (V)	C_T f = 1MHz MAX (PF)	C_T f = 1MHz VR (V)	t_{rr} MAX (ns)		PACKAGE
KDS 1553	70	300	100	300	150	1.4	-100	0.5	60	3.5	0	4	V_R = 6V	DO-35
KDS 1554	55								50				RL = 100Ω	
KDS 1555	35								30				I_F = 10mA	
IN 4148	75	225	75	500	175	1.0	10	0.025	20	4.0	0	4		

2. TEMPERATURE & BIAS COMPENSATION

SPEC / DEVICE	V_R (V)	I_{FM} (mA)	I_{FAV} (mA)	T_j (°C)	V_F MIN (V)	V_F TYP (V)	V_F MAX (V)	V_F I_F (mA)	I_R MAX (uA)	I_R V_R (V)	V_F TYP mV/°C	V_F I_F (mA)	PACKAGE
KDS 8513A-0	5	150	50	150	0.63	0.65	0.68	3	10	5	-2.0	1	DO-35

3. AFC FOR FM RECEIVER

SPEC / DEVICE	V_R (V)	T_j (°C)	I_R MAX (nA)	I_R V_R (V)	C_r MIN (PF)	C_r MAX (PF)	C_r V_R (V)	C_r f (MHz)	K MIN	K MAX	Q f=50MHz TYP	Q f=50MHz V_r (V)	PACKAGE
KDS 2236	15	150	100	4	7	14	4	1	0.21	0.50	120	4	DO-35

$$K = \frac{C_r\,(VR = 2V) - C_r\,(VR = 4V)}{C_r\,(VR = 4V)} \text{ at } f = 1MHz$$

4. GENERAL PURPOSE RECTIFIER

SPEC / DEVICE	V_{RM} (V)	V_{RSM} (V)	I_O (A)	I_{SURGE} (A)	T_j (°C)	Tstg (°C)	V_F MAX (V)	V_F I_F (A)	I_R MAX (uA)	I_R V_{RM} (V)	PACKAGE
IN 4001	50	100	1	50	175	-65-175	1.1	1	10	RATED	DO-41
IN 4002	100	200		50							
IN 4003	200	300		50							
IN 4004	400	500		50							
IN 4005	600	750		30							
IN 4006	800	1000		30							
IN 4007	1000	1200		30							

5. FAST RECOVERY RECTIFIER

SPEC / DEVICE	V_{RRM} (V)	T_j (°C)	Tstg (°C)	I_O (A)	@ V_F	V_F (V)	MAX I_F (A)	I_R (μA)	MAX @V_{RRM}	trr (ns)	MAX @	PACKAGE
KDR 812	200	150	-40~150	1	at RATED Tamb 75°C	1	1	1	at RATED	300		F-126
KDR 814	400											
KDR 816	600											
KDR 818	1000											

6. ZENER DIODE

SYMBOL	V_{ZT}			r_{ZT}	r_{ZK}	I_R	@ V_R	∝ V_Z	I_{ZM}	P_{tot}	T_j	PACKAGE
CHARAC-TERISTIC	Zener Voltage @ I_{ZT} = 5 mA			Maximum Zener Impedance @ I_{ZT} = 5 mA	Maximum Zener Knee Impedance @IZK = 1 mA	Reverse Current @ V_R Tamb 25°C	Reverse Voltage	Typical Temperature Coefficient 05 V_{ZT}	Maximum Zener Current	Allowable Power Dissipation	Junction Temperature	
UNIT	V			Ω	Ω	μA	V	%/°C	mA	mw	°C	
LIMITS / DEVICE	MIN	TYP	MAX	MAX	MAX	MAX	MAX	TYP	MAX	MAX	MAX	
BZX83-C4V7	4.4	4.7	5.0	80	600	2	1	-0.01	85	500	75	DO-35
BZX83-C5V6	5.2	5.6	6.0	40	450	1	1	0.03	70			
BZX83-C6V2	5.8	6.2	6.6	10	200	1	2	0.04	64			
BZX83-C7V5	7.0	7.5	7.9	7	50	1	3.5	0.05	53			
BZX83-C8V2	7.7	8.2	8.7	7	50	1	4	0.06	47			
BZX83-C9V1	8.5	9.1	9.6	10	50	1	5	0.06	43			
BZX83-C10	9.4	10	10.6	15	70	1	6	0.07	40			

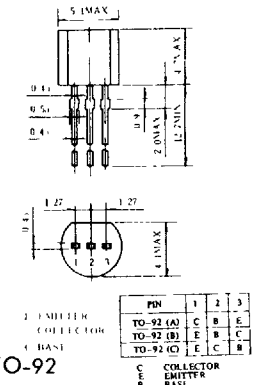
7. GERMANIUM TUNGSTEN DIODE

(AM/FM DETECTOR)

SPEC / DEVICE	USE	V_{RM} (V)	I_{FM} (mA)	I_{FS} (mA)	I_O (mA)	IF (mA)	MIN @V_F (V)	I_R (μA)	MAX @V_R (V)	C_j (PF)	TYP @ f (MHz)	PACKAGE
IN 60 M	AM	-24	70	200	20	3	1	100	-10	0.8	1	DO-7
IN 60 S	FM	-45	70	500	50	4	1	75	-10	0.8	1	DO-7

DIMENSION

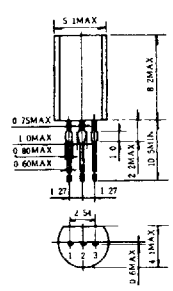
T-91-20



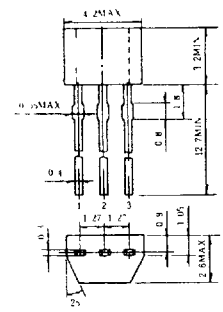
PIN	1	2	3
TO-92 (A)	C	B	E
TO-92 (B)	E	B	C
TO-92 (C)	E	C	B

C COLLECTOR
E EMITTER
B BASE

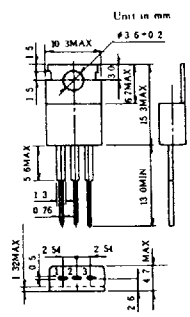
TO-92



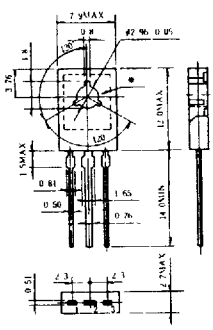
TO-92L



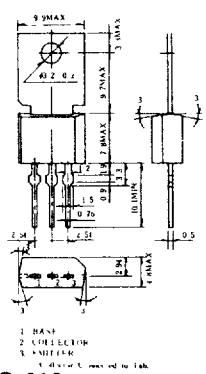
2-4EIA



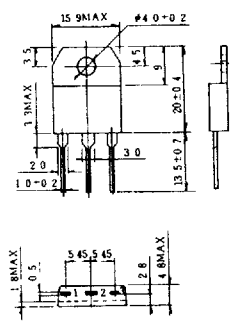
TO-220



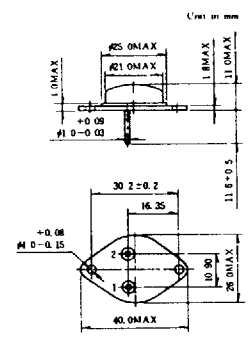
TO-126



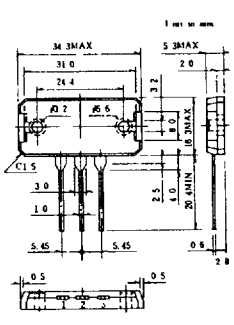
TO-202



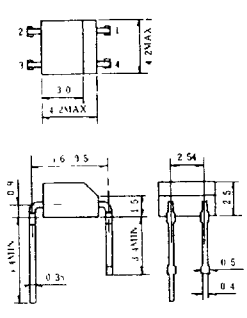
TO-3P



TO-3



TO-3P-II



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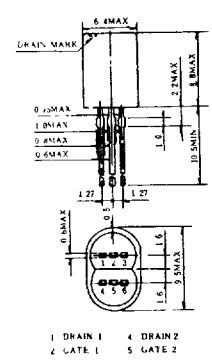
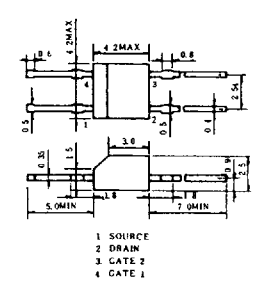
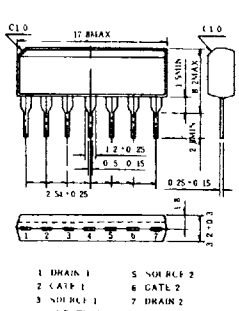


2-6EIA



2-4DIB



2-18AIA

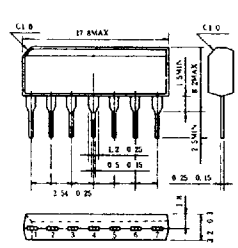


Fig. 1 (SIP 7pin)

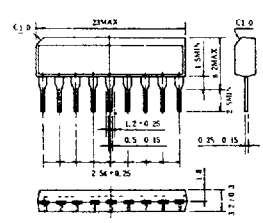


Fig. 2 (SIP 9pin)

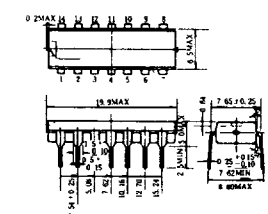


Fig. 3 (DIP 14pin)

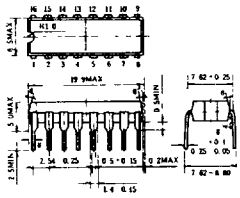


Fig. 4 (DIP 16pin)

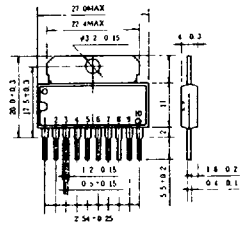


Fig. 5 (SIP 10pin)

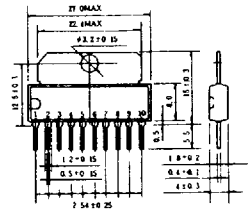


Fig. 6 (S-SIP 10pin)

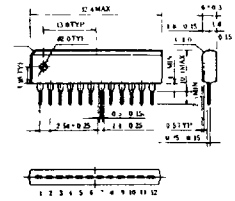


Fig. 7 (SIP-12pin)

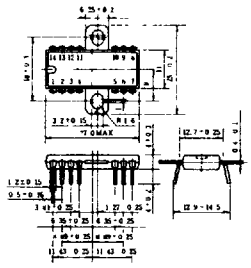


Fig. 8 (DIP 14pin)

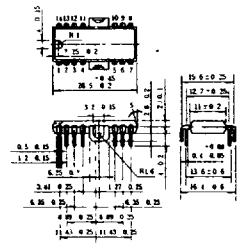


Fig. 9 (DIP 14pin)

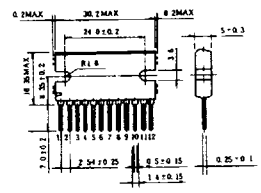


Fig. 10 (L-SIP-12pin)

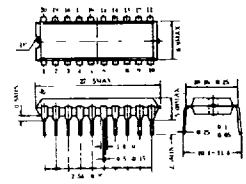


Fig. 11 (DIP 20pin)

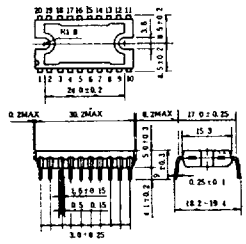


Fig. 12 (L-DIP-20pin)

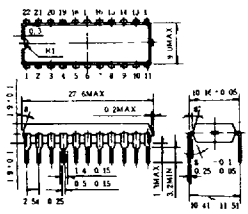


Fig. 13 (L-DIP-22pin)

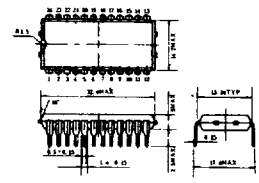


Fig. 14 (DIP 24pin)

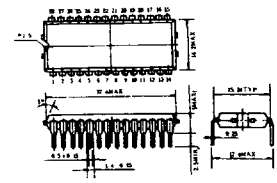


Fig. 15 (DIP 28pin)

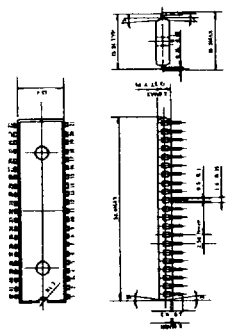
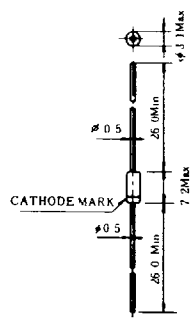
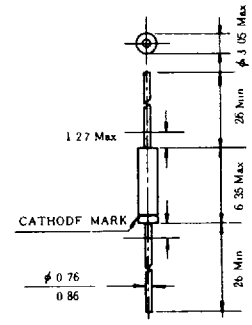


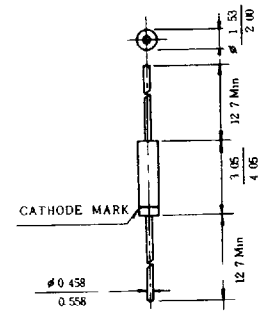
Fig. 16 (DIP 42pin)



DO-7



DO-35



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